

FDI8442

N-Channel PowerTrench® MOSFET

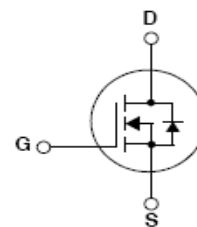
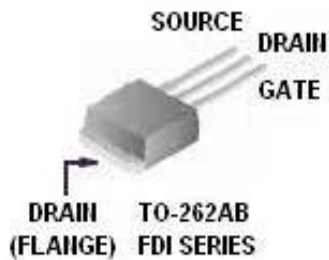
40V, 80A, 2.9mΩ

Features

- Typ $r_{DS(on)}$ = 2.3mΩ at $V_{GS} = 10V$, $I_D = 80A$
- Typ $Q_{g(10)}$ = 181nC at $V_{GS} = 10V$
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- Qualified to AEC Q101
- RoHS Compliant

Applications

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Electronic Steering
- Integrated Starter / Alternator
- Distributed Power Architectures and VRMs
- Primary Switch for 12V Systems



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|----------------|---|--------------|---------------------------|
| V_{DSS} | Drain to Source Voltage | 40 | V |
| V_{GS} | Gate to Source Voltage | ± 20 | V |
| I_D | Drain Current Continuous ($T_C < 158^\circ\text{C}$, $V_{GS} = 10\text{V}$) | 80 | A |
| | Drain Current Continuous ($T_{amb} = 25^\circ\text{C}$, $V_{GS} = 10\text{V}$, with $R_{\theta JA} = 62^\circ\text{C/W}$) | 23 | |
| | Pulsed | See Figure 4 | |
| E_{AS} | Single Pulse Avalanche Energy (Note 1) | 720 | mJ |
| P_D | Power Dissipation | 254 | W |
| | Derate above 25°C | 1.7 | $\text{W}/^\circ\text{C}$ |
| T_J, T_{STG} | Operating and Storage Temperature | -55 to +175 | $^\circ\text{C}$ |

Thermal Characteristics

| | | | |
|-----------------|---|------|--------------------|
| $R_{\theta JC}$ | Thermal Resistance Junction to Case | 0.59 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance Junction to Ambient (Note 2) | 62 | $^\circ\text{C/W}$ |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|---------|---------|-----------|------------|----------|
| FDI8442 | FDI8442 | TO-262 | Tube | N/A | 50 units |

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|------------|-----------------------------------|--|----|---|-----------|---------------|
| B_{VDSS} | Drain to Source Breakdown Voltage | $I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$ | 40 | - | - | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 32\text{V}$ $V_{GS} = 0\text{V}$ $T_J = 150^\circ\text{C}$ | - | - | 1 | μA |
| I_{GSS} | Gate to Source Leakage Current | $V_{GS} = \pm 20\text{V}$ | - | - | ± 100 | nA |

On Characteristics

| | | | | | | |
|--------------|----------------------------------|---|---|-----|-----|------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$ | 2 | 2.9 | 4 | V |
| $r_{DS(on)}$ | Drain to Source On Resistance | $I_D = 80\text{A}$, $V_{GS} = 10\text{V}$ | - | 2.3 | 2.9 | m Ω |
| | | $I_D = 80\text{A}$, $V_{GS} = 10\text{V}$, $T_J = 175^\circ\text{C}$ | - | 3.9 | 5.0 | |

Dynamic Characteristics

| | | | | | | | |
|--------------|----------------------------------|---|---|-------|-----|----------|----|
| C_{iss} | Input Capacitance | $V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$ | - | 12200 | - | pF | |
| C_{oss} | Output Capacitance | | - | 1040 | - | pF | |
| C_{rss} | Reverse Transfer Capacitance | | - | 640 | - | pF | |
| R_G | Gate Resistance | $V_{GS} = 0.5\text{V}$, $f = 1\text{MHz}$ | - | 1.0 | - | Ω | |
| $Q_{g(TOT)}$ | Total Gate Charge at 10V | $V_{GS} = 0$ to 10V | $V_{DD} = 20\text{V}$ $I_D = 80\text{A}$ $I_g = 1\text{mA}$ | - | 181 | 235 | nC |
| $Q_{g(TH)}$ | Threshold Gate Charge | $V_{GS} = 0$ to 2V | | - | 23 | 30 | nC |
| Q_{gs} | Gate to Source Gate Charge | | | - | 49 | - | nC |
| Q_{gs2} | Gate Charge Threshold to Plateau | | | - | 26 | - | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | | - | 41 | - | nC |

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Switching Characteristics

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------------|---------------------|--|-----|------|-----|-------|
| $t_{(on)}$ | Turn-On Time | $V_{DD} = 20\text{V}$, $I_D = 80\text{A}$ $V_{GS} = 10\text{V}$, $R_{GS} = 2\Omega$ | - | - | 62 | ns |
| $t_{d(on)}$ | Turn-On Delay Time | | - | 19.5 | - | ns |
| t_r | Turn-On Rise Time | | - | 19.3 | - | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | - | 57 | - | ns |
| t_f | Turn-Off Fall Time | | - | 17.2 | - | ns |
| t_{off} | Turn-Off Time | | - | - | 118 | ns |

Drain-Source Diode Characteristics

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|----------|-------------------------------|--|-----|-----|------|-------|
| V_{SD} | Source to Drain Diode Voltage | $I_{SD} = 80\text{A}$ | - | 0.9 | 1.25 | V |
| | | $I_{SD} = 40\text{A}$ | - | 0.8 | 1.0 | V |
| t_{rr} | Reverse Recovery Time | $I_F = 75\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$ | - | 49 | 64 | ns |
| Q_{rr} | Reverse Recovery Charge | $I_F = 75\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$ | - | 70 | 91 | nC |

Notes:

- 1: Starting $T_J = 25^\circ\text{C}$, $L = 0.35\text{mH}$, $I_{AS} = 64\text{A}$
 2: Pulse width = 100s.

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: <http://www.aecouncil.com/>
 All Fairchild Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

Typical Characteristics

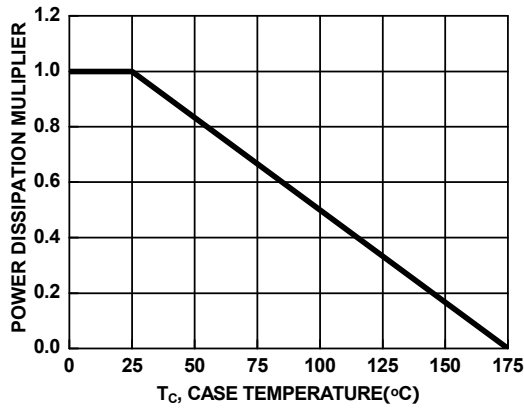


Figure 1. Normalized Power Dissipation vs Case Temperature

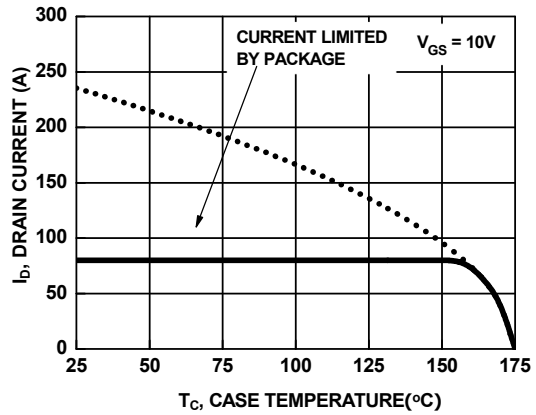


Figure 2. Maximum Continuous Drain Current vs Case Temperature

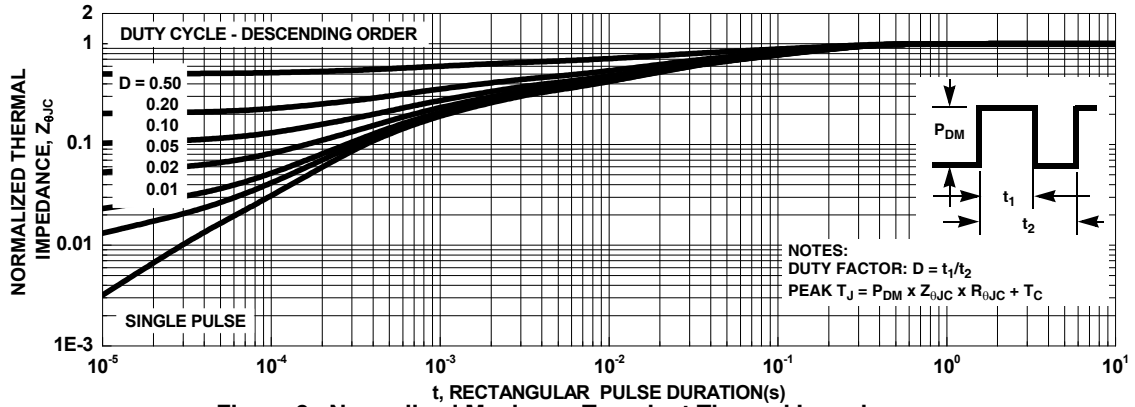


Figure 3. Normalized Maximum Transient Thermal Impedance

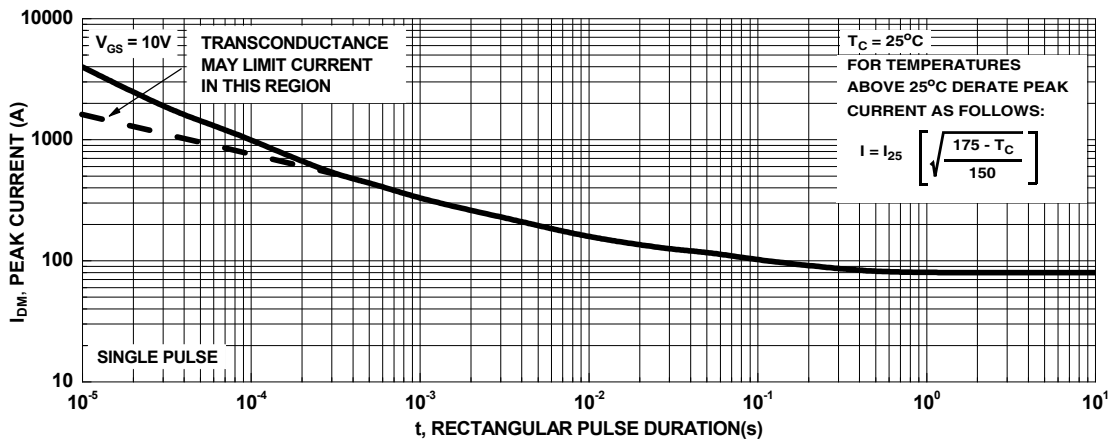


Figure 4. Peak Current Capability

Typical Characteristics

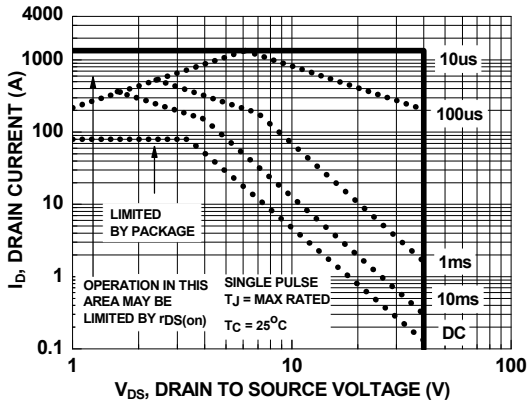
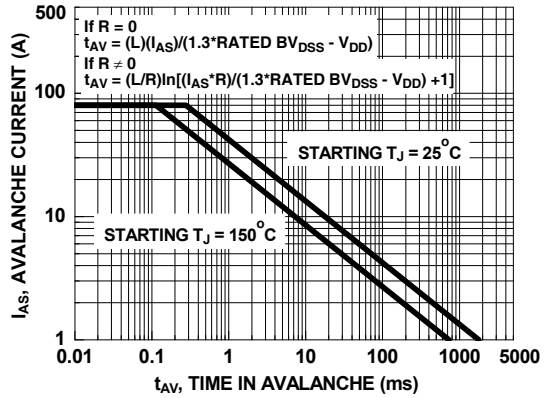


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

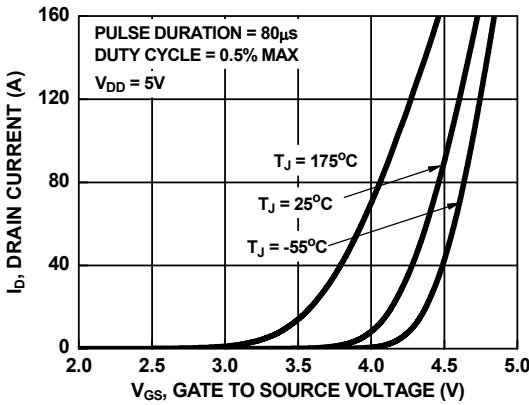


Figure 7. Transfer Characteristics

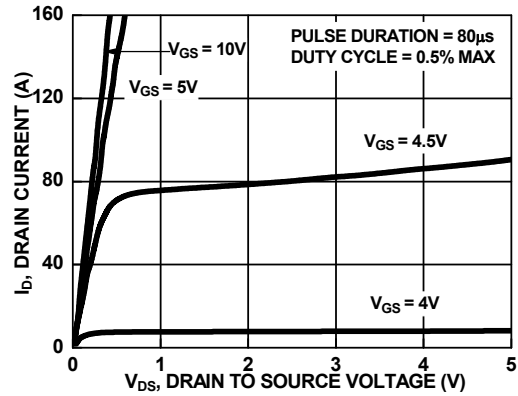


Figure 8. Saturation Characteristics

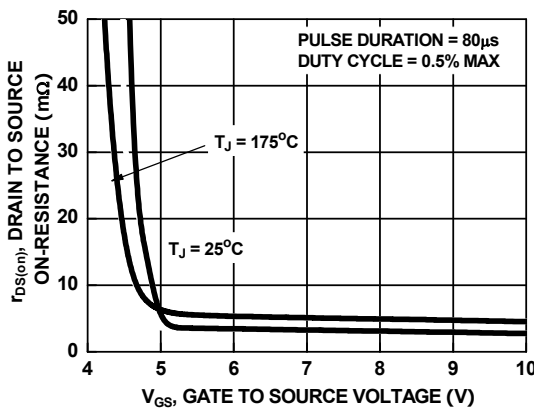


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

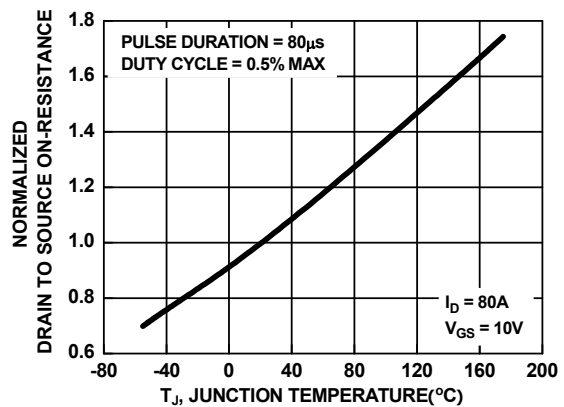


Figure 10. Normalized Drain to Source On-Resistance vs Junction Temperature

Typical Characteristics

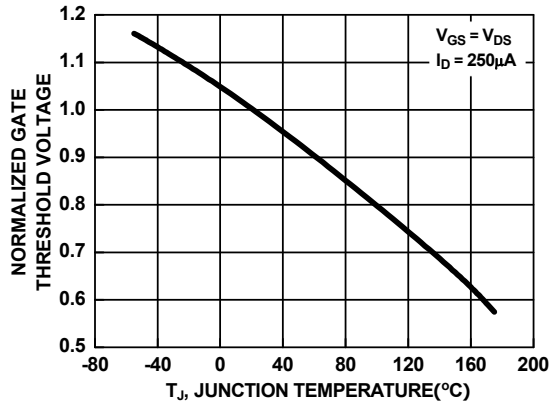


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

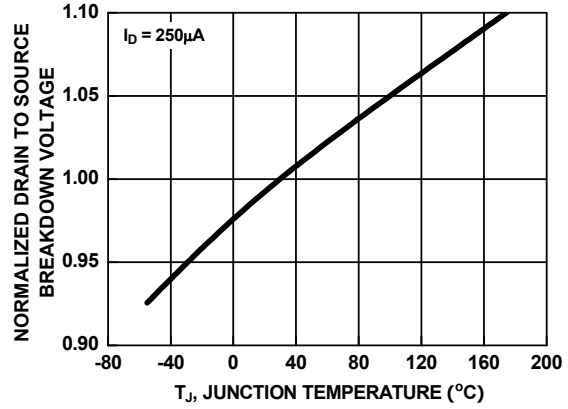


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

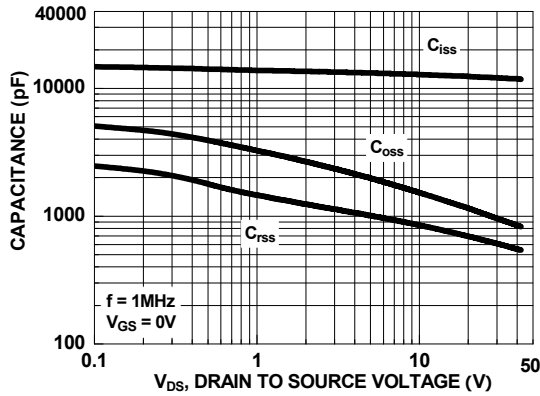


Figure 13. Capacitance vs Drain to Source Voltage

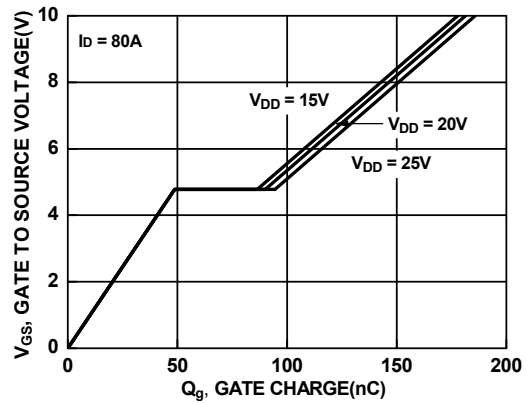


Figure 14. Gate Charge vs Gate to Source Voltage



TRADEMARKS

The following are registered and unregistered trademarks and service marks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

- | | | | |
|--------------------------------------|--|--|----------------------------------|
| ACEx [®] | Green FPS [™] | Power247 [®] | SuperSOT [™] -8 |
| Build it Now [™] | Green FPS [™] e-Series [™] | POWEREDGE [®] | SyncFET [™] |
| CorePLUS [™] | GTO [™] | Power-SPM [™] | The Power Franchise [®] |
| CROSSVOLT [™] | i-Lo [™] | PowerTrench [®] | the power franchise |
| CTL [™] | IntelliMAX [™] | Programmable Active Droop [™] | TinyBoost [™] |
| Current Transfer Logic [™] | ISOPLANAR [™] | QFET [®] | TinyBuck [™] |
| EcoSPARK [®] | MegaBuck [™] | QS [™] | TinyLogic [®] |
| F [®] | MICROCOUPLER [™] | QT Optoelectronics [™] | TINYOPTO [™] |
| Fairchild [®] | MicroFET [™] | Quiet Series [™] | TinyPower [™] |
| Fairchild Semiconductor [®] | MicroPak [™] | RapidConfigure [™] | TinyPWM [™] |
| FACT Quiet Series [™] | MillerDrive [™] | SMART START [™] | TinyWire [™] |
| FACT [®] | Motion-SPM [™] | SPM [®] | µSerDes [™] |
| FAST [®] | OPTOLOGIC [®] | STEALTH [™] | UHC [®] |
| FastvCore [™] | OPTOPLANAR [®] | SuperFET [™] | UniFET [™] |
| FPS [™] |  [®] | SuperSOT [™] -3 | VCX [™] |
| FRFET [®] | PDP-SPM [™] | SuperSOT [™] -6 | |
| Global Power Resource SM | Power220 [®] | | |

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

| Datasheet Identification | Product Status | Definition |
|--------------------------|------------------------|--|
| Advance Information | Formative or In Design | This datasheet contains the design specifications for product development. Specifications may change in any manner without notice. |
| Preliminary | First Production | This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design. |
| No Identification Needed | Full Production | This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design. |
| Obsolete | Not In Production | This datasheet contains specifications on a product that has been discontinued by Fairchild Semiconductor. The datasheet is printed for reference information only. |